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<p>1) Overview</p> <ul style="list-style-type: none"> • Table of Contents • List of Figures and Tables • Introduction • Process Summary 	
<p>2) Device Overview</p> <ul style="list-style-type: none"> • Package and Die • Die photo • Transistor Plan View • SEM cross section through measured transistors 	<ul style="list-style-type: none"> • Provide physically measured L & W from plan view and cross-section
<p>3) Transistor Analysis</p> <ul style="list-style-type: none"> • General Output characteristics • Subthreshold Swing curves • Transconductance • Extrapolated threshold voltage • Punchthrough characteristics • Gate and substrate leakage • Body Effect 	<ul style="list-style-type: none"> • Characteristics listed are typical • Actual curves provided will depend on device type • Typically 2 x NMOS and 2 x PMOS transistors will be measured
<p>4) Transistor Summary</p> <ul style="list-style-type: none"> • Summary table of electrical parameters for each measured transistor 	

Please note that Chipworks report content may vary, as reports published prior to the latest revision date may contain different content than stated above.

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